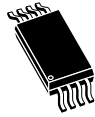


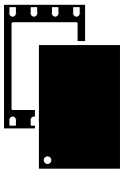
## 32-Kbit serial I<sup>2</sup>C bus EEPROM



SO8N (MN)  
150 mil width



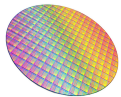
TSSOP8 (DW)  
169 mil width



UFDFPN8 (MC)  
DFN8 - 2x3 mm



UFDFPN5 (MH)  
DFN5 - 1.7x1.4 mm



Unsaan wafer



WLCSP4 (CU)

### Features

#### I<sup>2</sup>C interface

- Compatible with following I<sup>2</sup>C bus modes:
  - 1 MHz (fast mode plus)
  - 400 kHz (fast mode)
  - 100 kHz (standard mode)

#### Memory

- 32 Kbit (4 Kbyte) of EEPROM
- Page size: 32 bytes
- Additional 32-byte identification page for M24C32-D only

#### Power supply

- Wide voltage range:
  - From 1.7 V to 5.5 V over -40 °C to +85 °C
  - From 1.6 V to 5.5 V under temperature constraint

#### Temperature

- Operating temperature range: From -40 °C up to +85 °C

#### Fast write cycle time

- Byte and page write within 5 ms (3.2 ms typical)

#### Performance

- Enhanced ESD/latch-up protection
- More than 4 million write cycles
- More than 200-year data retention

#### Advanced features

- Hardware write protection of the whole memory array
- Random and sequential read modes

#### Package

- SO8N, TSSOP8, UFDFPN8, and UFDFPN5 (ECOPACK2)
- WLCSP4 4-ball
- Unsaan wafer (each die is tested)

#### Product status link

[M24C32-R](#)

[M24C32-F](#)

[M24C32-DF](#)

[M24C32-X](#)

[M24C32-W](#)

#### Product label



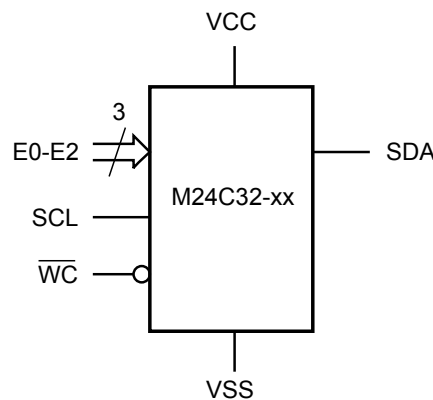
# 1 Description

The M24C32 is a 32-Kbit I2C-compatible EEPROM (electrically erasable programmable memory) organized as 4 K × 8 bits.

The M24C32-W can operate with a supply voltage from 2.5 V to 5.5 V, the M24C32-R can operate with a supply voltage from 1.8 V to 5.5 V, and the M24C32-F and M24C32-DF can operate with a supply voltage from 1.7 V to 5.5 V, over an ambient temperature range of -40 °C / +85 °C; while the M24C32-X can operate with a supply voltage from 1.6 V to 5.5 V over an ambient temperature range of -20 °C / +85 °C.

The M24C32-D offers an additional page, named the identification page (32 byte). The identification page can be used to store sensitive application parameters which can be (later) permanently locked in read-only mode.

**Figure 1. Logic diagram**

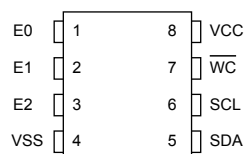


DT70958

**Table 1. Signal names**

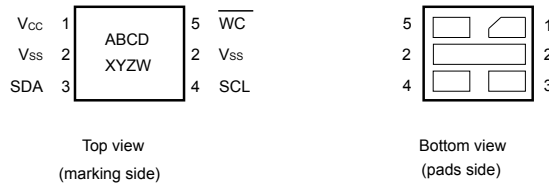
Signal name	Function	Direction
E2, E1, E0	Chip enable	Input
SDA	Serial data	I/O
SCL	Serial clock	Input
$\overline{WC}$	Write control	Input
V <sub>CC</sub>	Supply voltage	-
V <sub>SS</sub>	Ground	-

**Figure 2. 8-pin package connections, top view**



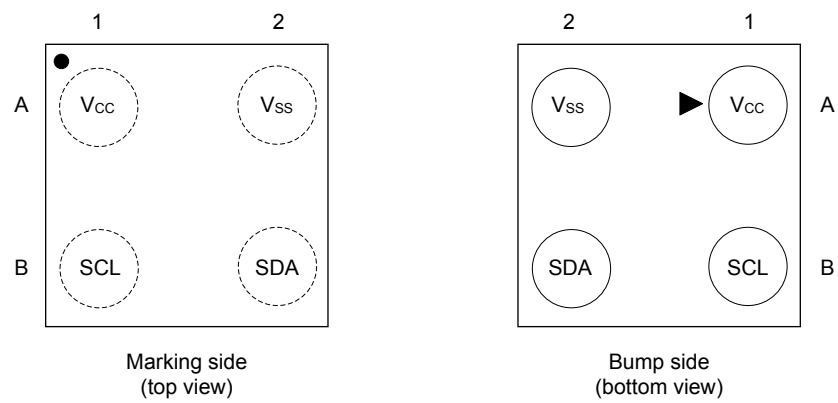
DT70957

Figure 3. UDFPN5 (DFN5) package connections



- Inputs E2, E1, E0 are not connected, therefore read as (000). Please refer to Section 2.3 for further explanations.

Figure 4. WLCSP 4 bump package connections



DT70959

- Inputs E2, E1, E0 are read as (000). Please refer to Section 2.3 for further explanations.

Table 2. Signals vs. bump position

Position	A	B
1	V <sub>CC</sub>	SCL
2	V <sub>SS</sub>	SDA

## 2 Signal description

### 2.1 Serial clock (SCL)

The signal applied on the SCL input is used to strobe the data available on SDA(in) and to output the data on SDA(out).

### 2.2 Serial data (SDA)

SDA is an input/output used to transfer data in or data out of the device. SDA(out) is an open drain output that may be wired-AND with other open drain or open collector signals on the bus. A pull-up resistor must be connected from serial data (SDA) to  $V_{CC}$  (Figure 15 and Figure 16 indicate how to calculate the value of the pull-up resistor).

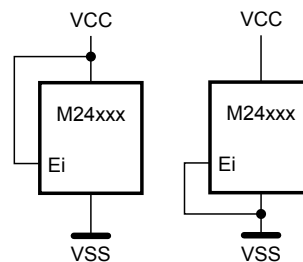
### 2.3 Chip enable (E2, E1, E0)

(E2,E1,E0) input signals are used to set the value that is to be looked for on the three least significant bits (b3, b2, b1) of the 7-bit device select code (see Table 3). These inputs must be tied to  $V_{CC}$  or  $V_{SS}$ , as shown in Figure 5. When not connected (left floating), these inputs are read as low (0).

For the UDFPN5 package, the (E2,E1,E0) inputs are not connected, therefore read as (0,0,0).

For the 4-balls WLCSP package (see Figure 4), the (E2,E1,E0) inputs are internally connected to (0, 0, 0).

Figure 5. Chip enable inputs connection



DS70960

### 2.4 Write control ( $\overline{WC}$ )

This input signal is useful for protecting the entire contents of the memory from inadvertent write operations. Write operations are disabled to the entire memory array when write control ( $\overline{WC}$ ) is driven high. Write operations are enabled when write control ( $\overline{WC}$ ) is either driven low or left floating.

When write control ( $\overline{WC}$ ) is driven high, device select and address bytes are acknowledged, data bytes are not acknowledged.

### 2.5 $V_{SS}$ (ground)

$V_{SS}$  is the reference for the  $V_{CC}$  supply voltage.

### 2.6 Supply voltage ( $V_{CC}$ )

#### 2.6.1 Operating supply voltage ( $V_{CC}$ )

Prior to selecting the memory and issuing instructions to it, a valid and stable  $V_{CC}$  voltage within the specified [ $V_{CC}(\min)$ ,  $V_{CC}(\max)$ ] range must be applied (see operating conditions in Section 8 DC and AC parameters). In order to secure a stable DC supply voltage, it is recommended to decouple the  $V_{CC}$  line with a suitable capacitor (usually of the order of 10 nF to 100 nF) close to the  $V_{CC}/V_{SS}$  package pins.

This voltage must remain stable and valid until the end of the transmission of the instruction and, for a write instruction, until the completion of the internal write cycle ( $t_w$ ).

### 2.6.2 Power-up conditions

The  $V_{CC}$  voltage has to rise continuously from 0 V up to the minimum  $V_{CC}$  operating voltage (see operating conditions in [Section 8 DC and AC parameters](#)).

### 2.6.3 Device reset

In order to prevent inadvertent write operations during power-up, a power-on-reset (POR) circuit is included.

At power-up, the device does not respond to any instruction until  $V_{CC}$  has reached the internal reset threshold voltage. This threshold is lower than the minimum  $V_{CC}$  operating voltage (see operating conditions in [Section 8 DC and AC parameters](#)). When  $V_{CC}$  passes over the POR threshold, the device is reset and enters the standby power mode; however, the device must not be accessed until  $V_{CC}$  reaches a valid and stable DC voltage within the specified [ $V_{CC}(\text{min})$ ,  $V_{CC}(\text{max})$ ] range (see operating conditions in [Section 8 DC and AC parameters](#)).

In a similar way, during power-down (continuous decrease in  $V_{CC}$ ), the device must not be accessed when  $V_{CC}$  drops below  $V_{CC}(\text{min})$ . When  $V_{CC}$  drops below the power-on-reset threshold voltage, the device stops responding to any instruction sent to it.

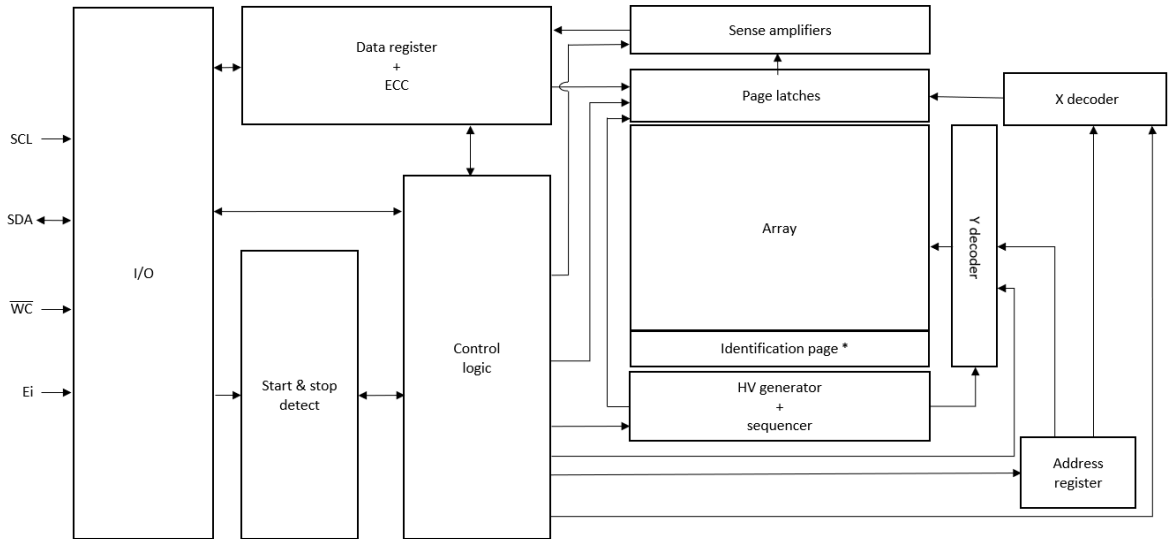
### 2.6.4 Power-down conditions

During power-down (continuous decrease in  $V_{CC}$ ), the device must be in the standby power mode (mode reached after decoding a stop condition, assuming that there is no internal write cycle in progress).

### 3 Memory organization

The memory is organized as shown below.

Figure 6. Block diagram

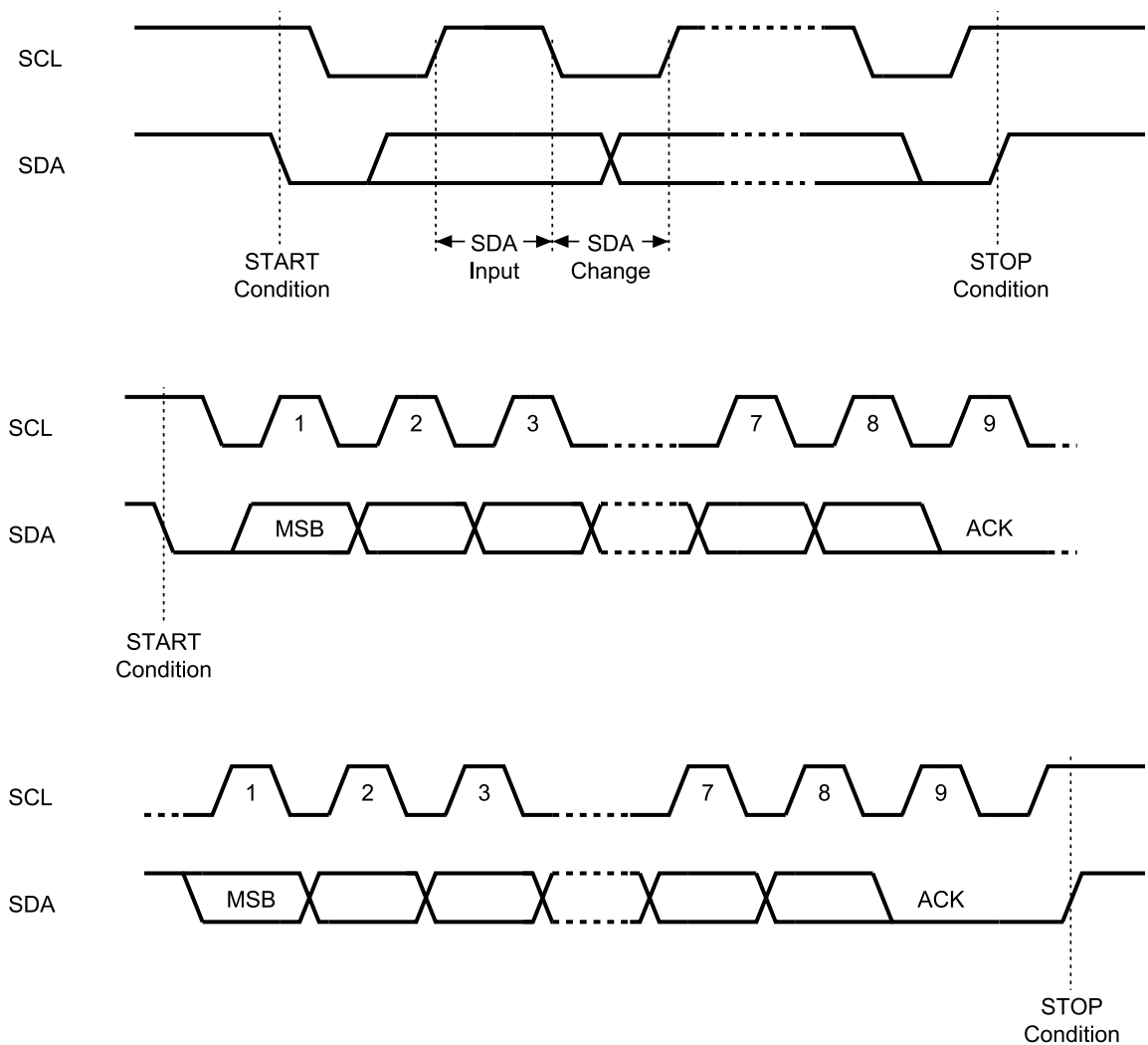


\*: For M24C32-DF only

## 4 Device operation

The device supports the I<sup>2</sup>C protocol. This is summarized in Figure 7. Any device that sends data on to the bus is defined to be a transmitter, and any device that reads the data to be a receiver. The device that controls the data transfer is known as the bus controller, and the other as the target device. A data transfer can only be initiated by the bus controller, which will also provide the serial clock for synchronization. The device is always a target in all communications.

Figure 7. I<sup>2</sup>C bus protocol



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### 4.1 Start condition

Start is identified by a falling edge of serial data (SDA) while serial clock (SCL) is stable in the high state. A start condition must precede any data transfer instruction. The device continuously monitors (except during a write cycle) serial data (SDA) and serial clock (SCL) for a start condition.

## 4.2 Stop condition

Stop is identified by a rising edge of serial data (SDA) while serial clock (SCL) is stable in the high state. A stop condition terminates communication between the device and the bus controller. A read instruction that is followed by NoAck can be followed by a stop condition to force the device into the standby mode.

A stop condition at the end of a write instruction triggers the internal write cycle.

## 4.3 Data input

During data input, the device samples serial data (SDA) on the rising edge of serial clock (SCL). For correct device operation, serial data (SDA) must be stable during the rising edge of serial clock (SCL), and the serial data (SDA) signal must change only when serial clock (SCL) is driven low.

## 4.4 Acknowledge bit (ACK)

The acknowledge bit is used to indicate a successful byte transfer. The bus transmitter, whether it be bus controller or target device, releases serial data (SDA) after sending eight bits of data. During the 9<sup>th</sup> clock pulse period, the receiver pulls serial data (SDA) low to acknowledge the receipt of the eight data bits.

## 4.5 Device addressing

To start communication between the bus controller and the target device, the bus controller must initiate a Start condition. Following this, the bus controller sends the device select code and byte address as specified in [Table 3](#), [Table 4](#), and [Table 5](#).

When the device select code is received, the device only responds if the chip enable address is the same as the value on its chip enable E2, E1, E0 inputs.

The 8<sup>th</sup> bit is the read/write bit (RW). This bit is set to 1 for read and 0 for write operations.

If a match occurs on the device select code, the corresponding device gives an acknowledgment on serial data (SDA) during the 9<sup>th</sup> bit time. If the device does not match the device select code, the device deselected itself from the bus, and goes into standby mode.



**Table 3. Device select code**

Features	Device type identifier bits				Chip enable address <sup>(1)</sup>			R/W
	Bit 7 <sup>(2)</sup>	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0 <sup>(3)</sup>
Memory	1	0	1	0	E2	E1	E0	R/W
Identification page	1	0	1	1	E2	E1	E0	R/W
Identification page lock	1	0	1	1	E2	E1	E0	R/W

1. E0, E1 and E2 are compared with the value read on input pins E0, E1 and E2.
2. MSB is sent first.
3. LSB

**Table 4. First byte address**

Features	Bit 7 <sup>(1)</sup>	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Memory	X	X	X	X	A11	A10	A9	A8
Identification page	X	X	X	X	X	0	X	X
Identification page lock	X	X	X	X	X	1	X	X

1. MSB is sent first.

Note: X = Don't care.

**Table 5. Second byte address**

Features	Bit 7 <sup>(1)</sup>	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Memory	A7	A6	A5	A4	A3	A2	A1	A0
Identification page	X	X	X	A4	A3	A2	A1	A0
Identification page lock	X	X	X	X	X	X	X	X

1. MSB is sent first.

Note: X = Don't care.

## 5 Instructions

### 5.1 Write operations

Following a start condition the bus controller sends a device select code with the R/W bit (RW) reset to 0. The device acknowledges this, as shown in Figure 8, and waits for two address bytes. The device responds to each address byte with an acknowledge bit, and then waits for the data byte. See in Section 4.5 Device addressing (Table 3, Table 4, and Table 5) how to address the memory and the identification page.

When the bus controller generates a stop condition immediately after a data byte ack bit (in the “10<sup>th</sup> bit” time slot), either at the end of a byte write or a page write, the internal write cycle  $t_W$  is triggered. A stop condition at any other time slot does not trigger the internal write cycle.

After the stop condition and the successful completion of an internal write cycle ( $t_W$ ), the device internal address counter is automatically incremented to point to the next byte after the last modified byte.

During the internal write cycle, serial data (SDA) is disabled internally, and the device does not respond to any requests.

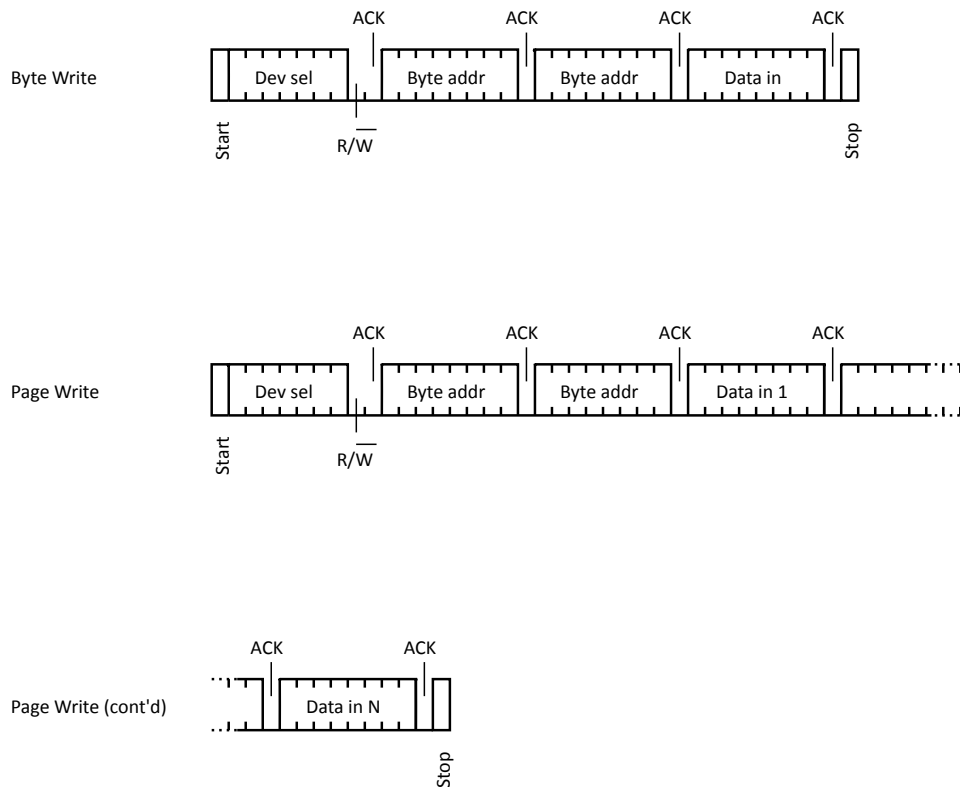
If the write control input ( $\overline{WC}$ ) is driven high, the write instruction is not executed and the accompanying data bytes are not acknowledged, as shown in Figure 9.

#### 5.1.1 Byte write

After the device select code and the address bytes, the bus controller sends one data byte.

If the addressed location is write-protected, by write control ( $\overline{WC}$ ) being driven high, the device replies with no ACK, and the location is not modified, as shown in Figure 9. If, instead, the addressed location is not write-protected, the device replies with ACK. The bus controller terminates the transfer by generating a stop condition, as shown in the figure below:

Figure 8. Write mode sequence with data write enabled



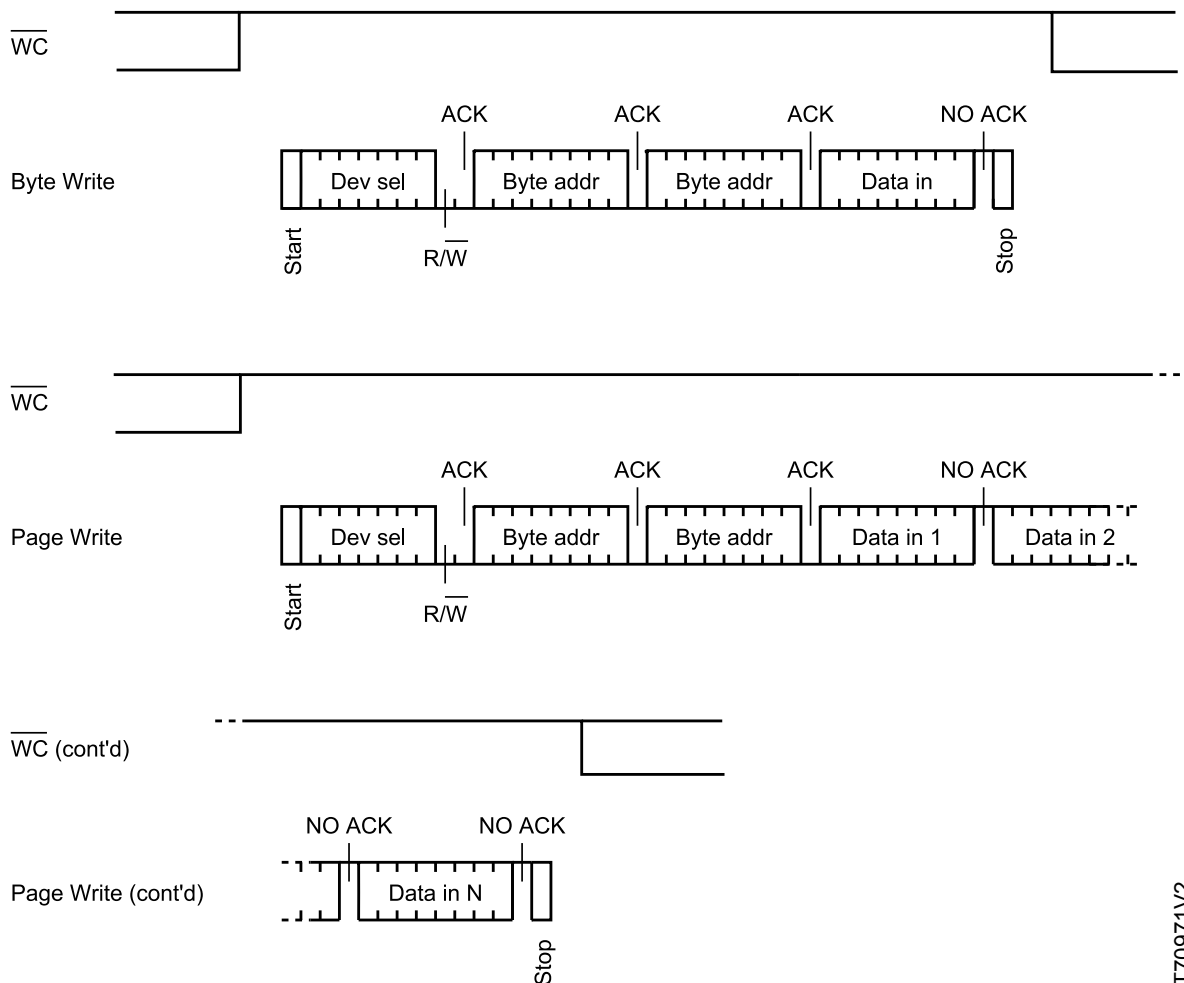
### 5.1.2 Page write

The page write mode allows up to 32 bytes to be written in a single write cycle, provided that they are all located in the same page in the memory: that is, the most significant memory address bits, A16-A5, are the same. If more bytes are sent than fit up to the end of the page, a “roll-over” occurs, that is, the bytes exceeding the page end are written on the same page, from location 0.

The bus controller sends from 1 to 32 byte of data, each of which is acknowledged by the device if write control (WC) is low. If write control (WC) is high, the contents of the addressed memory location are not modified, and each data byte is followed by a NoAck, as shown in Figure 9. After each transferred byte, the internal page address counter is incremented.

The transfer is terminated by the bus controller generating a stop condition.

Figure 9. Write mode sequences with  $\overline{WC} = 1$  (data write inhibited)



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### 5.1.3 Write identification page (M24C32-D only)

The identification page, is an additional 32- bytes page, which can be written and (later) permanently locked in read-only mode. It is written by issuing the write identification page instruction. This instruction uses the same protocol and format as page write (into memory array), except for the following differences:

- Device type identifier = 1011b
- MSB address bits A15 to A5 are don't care except for address bit A10, which must be '0'.
- LSB address bits A4 to A0 define the byte address inside the identification page.

If the identification page is locked, the data bytes transferred during the write identification page instruction are not acknowledged (NoAck).

### 5.1.4 Lock identification page (M24C32-D only)

The lock identification page instruction (lock ID) permanently locks the identification page in read-only mode. The lock ID instruction is similar to byte write (into memory array) with the following specific conditions:

- Device type identifier = 1011b
- Address bit A10 must be '1'; all other address bits are don't care
- The data byte must be equal to the binary value xxxx xx1x, where x is don't care.

### 5.1.5 ECC (error correction code) and write cycling

The ECC is offered only in devices identified with process letter K, all other devices (identified with a different process letter) do not embed the ECC logic.

The error correction code (ECC) is an internal logic function which is transparent for the I<sup>2</sup>C communication protocol.

The ECC logic is implemented on each group of four EEPROM bytes. Inside a group, if a single bit out of the four bytes happens to be erroneous during a read operation, the ECC detects this bit and replaces it with the correct value. The read reliability is therefore much improved.

Even if the ECC function is performed on groups of four bytes, a single byte can be written/cycled independently. In this case, the ECC function also writes/cycles the three other bytes located in the same group. As a consequence, the maximum cycling budget is defined at group level and the cycling can be distributed over the 4 bytes of the group: the sum of the cycles seen by byte0, byte1, byte2 and byte3 of the same group must remain below the maximum value defined [Table 7](#).

*Note:* A group of four bytes is located at addresses  $[4*N, 4*N+1, 4*N+2, 4*N+3]$ , where  $N$  is an integer.

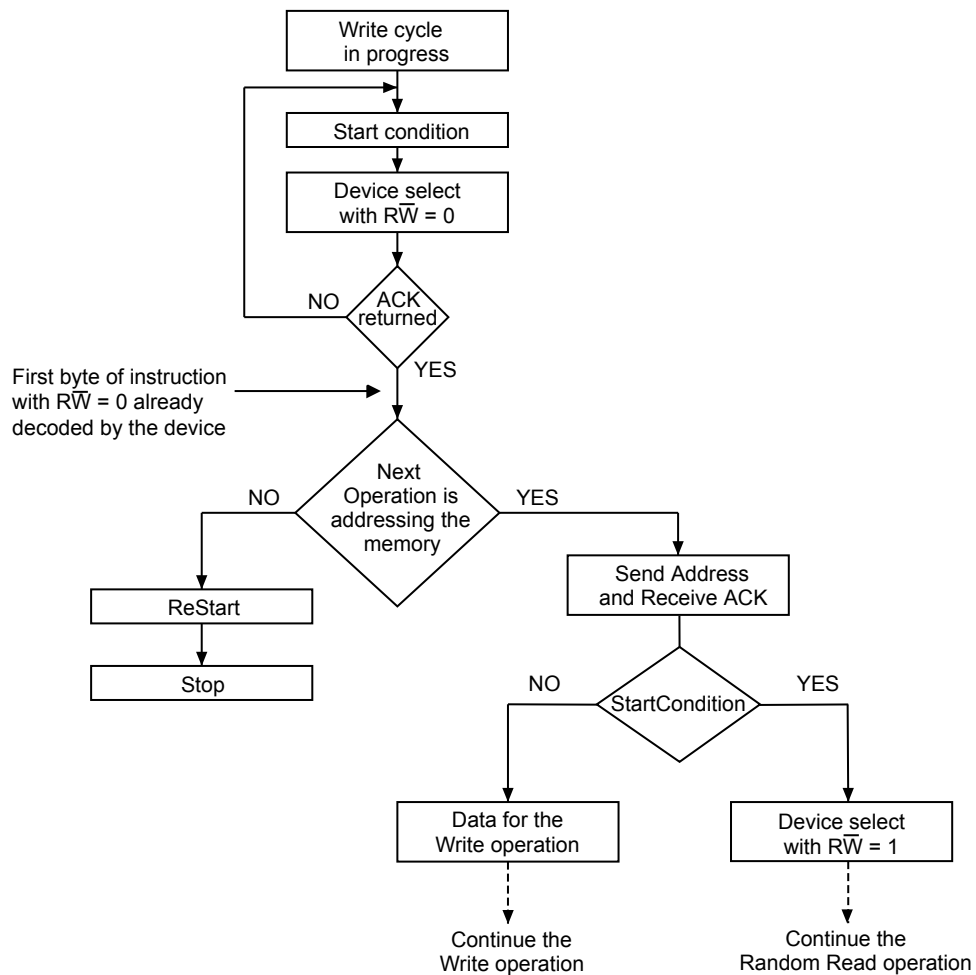
### 5.1.6 Minimizing write delays by polling on ACK

The maximum write time ( $t_{W}$ ) is shown in AC characteristics tables in Section 8 DC and AC parameters, but the typical time is shorter. To make use of this, a polling sequence can be used by the bus controller.

The sequence, as shown in Figure 10, is:

- Initial condition: a writing cycle is in progress.
- Step 1: the bus controller issues a start condition followed by a device select code (the first byte of the new instruction).
- Step 2: if the device is busy with the internal write cycle, no ack is returned and the bus controller goes back to step 1. If the device has terminated the internal write cycle, it responds with an ack, indicating that the device is ready to receive the second part of the instruction (the first byte of this instruction having been sent during step 1).

Figure 10. Write cycle polling flowchart using ACK



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**Note:** The seven most significant bits of the device select code of a random read (bottom right box in the figure) must be identical to the seven most significant bits of the device select code of the write (polling instruction in the figure).

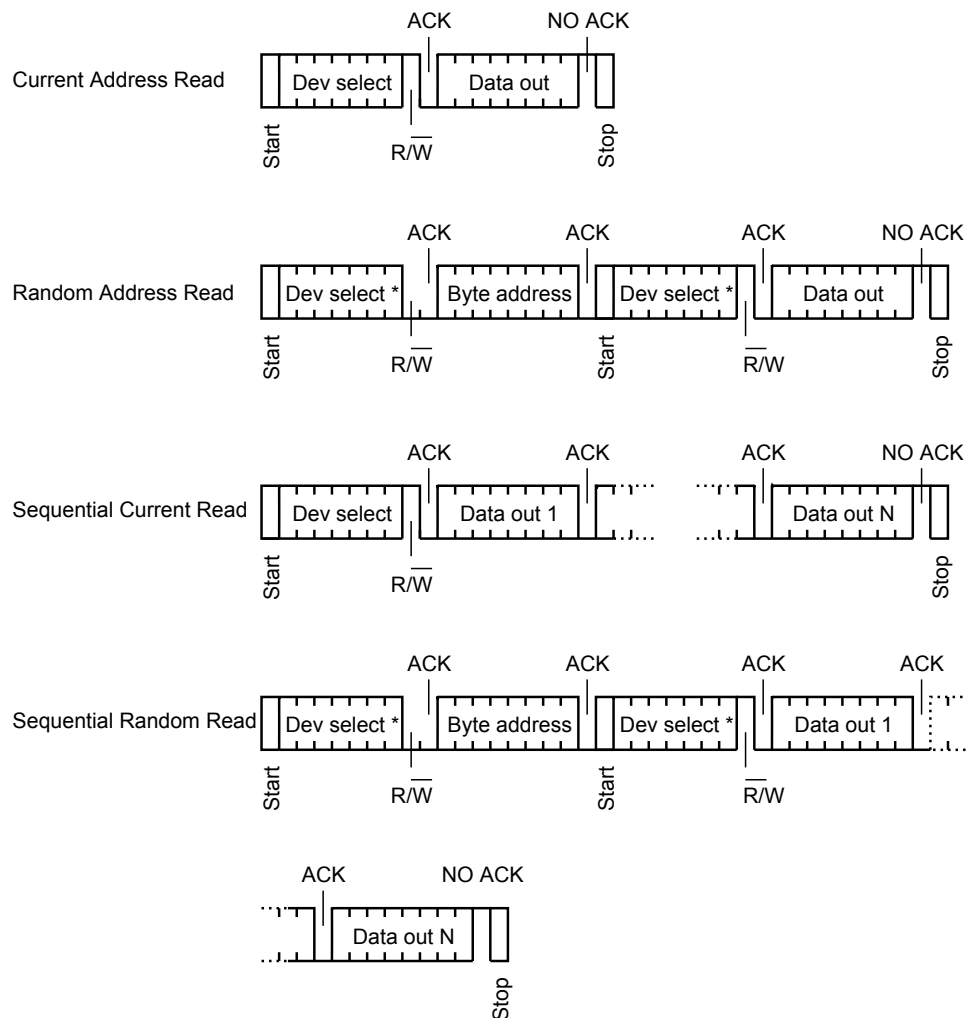
## 5.2 Read operations

Read operations are performed independently of the state of the write control ( $\overline{WC}$ ) signal.

After the successful completion of a read operation, the device internal address counter is incremented by one, to point to the next byte address.

For the read instructions, after each byte read (data out), the device waits for an acknowledgment (data in) during the 9<sup>th</sup> bit time. If the bus controller does not acknowledge during this 9<sup>th</sup> time, the device terminates the data transfer and switches to its standby mode after a stop condition.

**Figure 11. Read mode sequences**



DT01942bV1

### 5.2.1 Random address read

A dummy write is first performed to load the address into this address counter (as shown in Figure 11) but without sending a stop condition. Then, the bus controller sends another start condition, and repeats the device select code, with the  $\overline{RW}$  bit set to 1. The device acknowledges this, and outputs the contents of the addressed byte. The bus controller must not acknowledge the byte, and terminates the transfer with a stop condition.

### 5.2.2 Current address read

For the current address read operation, following a start condition, the bus controller only sends a device select code with the  $\overline{RW}$  bit set to 1. The device acknowledges this, and outputs the byte addressed by the internal address counter. The counter is then incremented. The bus controller terminates the transfer with a stop condition, as shown in Figure 11, without acknowledging the byte.

**Note:** *The address counter value is defined by instructions accessing either the memory, or the identification page. When accessing the identification page, the address counter value is loaded with the byte location, therefore the next current address read in the memory uses this new address counter value. When accessing the memory, it is safer to always use the random address read instruction (this instruction loads the address counter with the byte location to read in the memory, see [Section 5.2.1 Random address read](#)) instead of the current address read instruction.*

### 5.2.3 Sequential read

This operation can be used after a current address read or a random address read. The bus controller does acknowledge the data byte output, and sends additional clock pulses so that the device continues to output the next byte in sequence. To terminate the stream of bytes, the bus controller must not acknowledge the last byte, and must generate a stop condition, as shown in [Figure 11](#).

The output data comes from consecutive addresses, with the internal address counter automatically incremented after each byte output. After the last memory address, the address counter “rolls-over”, and the device continues to output data from the memory address 00h.

### 5.2.4 Read identification page (M24C32-D only)

The identification page is a 32-bytes additional page, which can be written and (later) permanently locked in read-only mode.

The identification page can be read by issuing a read identification page instruction. This instruction uses the same protocol and format as the random address read (from memory array) except for the following differences:

- Device type identifier = 1011b
- MSB address bits A15 to A8 are don't care
- LSB address bits A7 to A5 are don't care, bits A4 to A0 define the byte address inside the identification page.

The number of bytes to read in the ID page must not exceed the page boundary (e.g.: when reading the identification page from location 10d, the number of bytes should be less than or equal to 22, as the ID page boundary is 32 bytes).

### 5.2.5 Read the lock status (M24C32-D only)

The locked/unlocked status of the identification page can be checked by transmitting a specific truncated command [identification page write instruction + one data byte] to the device. The device returns an acknowledge bit if the identification page is unlocked, otherwise a NoAck bit if the identification page is locked.

Right after this, it is recommended to transmit to the device a start condition followed by a stop condition, so that:

- Start: the truncated command is not executed because the start condition resets the device internal logic,
- Stop: the device is then set back into standby mode by the stop condition

Figure 12. Read lock status (identification page unlocked)

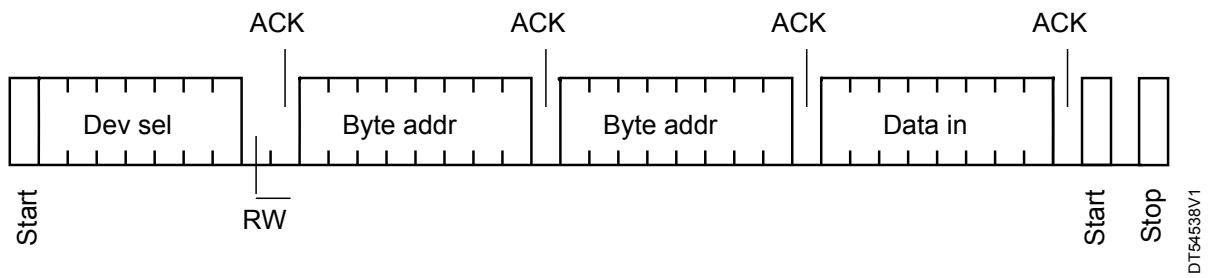
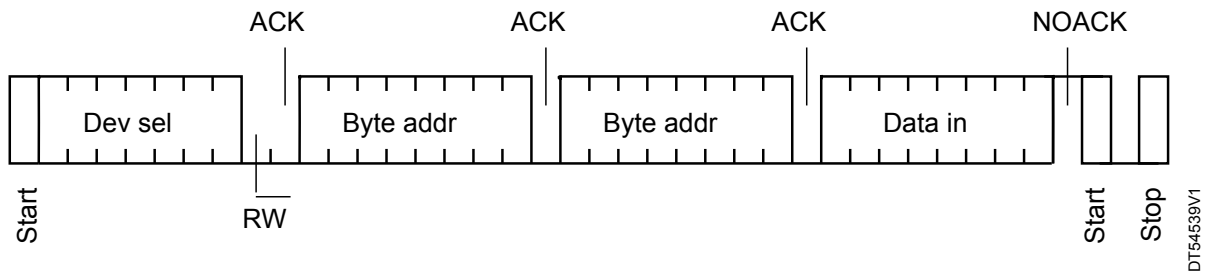


Figure 13. Read lock status (identification page locked)







## 6 Initial delivery state

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The packaged device is delivered with:

- All the memory array bits set to 1 (each byte contains FFh)
- All the identification page bits set to 1 (each byte contains FFh)

And when delivered in unsawn wafer :

- All the memory array bits set to 1 (each byte contains FFh) , except the last byte located at the address 0FFFh which is written with the value 22h.

## 7 Maximum rating

Stressing the device outside the ratings listed in Table 6 may cause permanent damage to the device. These are stress ratings only, and operation of the device at these, or any other conditions outside those indicated in the operating sections of this specification, is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Table 6. Absolute maximum ratings**

Symbol	Parameter	Min.	Max.	Unit
-	Ambient operating temperature	-40	130	°C
T <sub>STG</sub>	Storage temperature	-65	150	°C
T <sub>LEAD</sub>	Lead temperature during soldering	see note <sup>(1)</sup>		°C
I <sub>OL</sub>	DC output current (SDA = 0)	-	5	mA
V <sub>IO</sub>	Input or output range	-0.50	6.5	V
V <sub>CC</sub>	Supply voltage	-0.50	6.5	V
V <sub>ESD</sub>	Electrostatic pulse (human body model) <sup>(2)</sup>	-	3000 <sup>(3)</sup>	V

1. Compliant with JEDEC Std J-STD-020 (for small body, Sn-Pb or Pb-free assembly), the ST ECOPACK 7191395 specification, and the European directive on Restrictions of Hazardous Substances (RoHS directive 2011/65/EU of July 2011).
2. Positive and negative pulses applied on different combinations of pin connections, according to ANSI/ESDA/JEDEC JS-001, C1 = 100 pF, R1 = 1500 Ω, R2 = 500 Ω.
3. 4000 V for devices identified with process letter K.

## 8 DC and AC parameters

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device.

**Table 7. Operating conditions (voltage range W)**

Symbol	Parameter	Min.	Max.	Unit
$V_{CC}$	Supply voltage	2.5	5.5	V
$T_A$	Ambient operating temperature	-40	85	°C
$f_C$	Operating clock frequency	-	1	MHz

**Table 8. Operating conditions (voltage range R)**

Symbol	Parameter	Min.	Max.	Unit
$V_{CC}$	Supply voltage	1.8	5.5	V
$T_A$	Ambient operating temperature	-40	85	°C
$f_C$	Operating clock frequency	-	1	MHz

**Table 9. Operating conditions (voltage range F)**

Symbol	Parameter	Min.	Max.	Unit	
$V_{CC}$	Supply voltage	1.6 <sup>(1)</sup>	1.7	5.5	V
$T_A$	Ambient operating temperature: read	-40	-40	85	°C
	Ambient operating temperature: write	0	-40	85	°C
$f_C$	Operating clock frequency, $V_{CC} \geq 1.6$ V <sup>(1)</sup>	-	400	KHz	
	Operating clock frequency, $V_{CC} \geq 1.7$ V	-	1000	KHz	

1. Only for devices identified with process letter T

**Table 10. Operating conditions (voltage range X)**

Symbol	Parameter	Min.	Max.	Unit
$V_{CC}$	Supply voltage	1.6	5.5	V
$T_A$	Ambient operating temperature	-20	85	°C
$f_C$	Operating clock frequency	-	1	MHz

**Table 11. Input parameters**

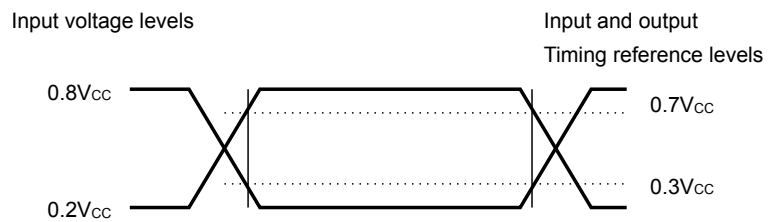
Symbol	Parameter	Test condition	Min.	Max.	Unit
$C_{IN}^{(1)}$	Input capacitance (SDA)	-	-	8	pF
$C_{IN}^{(1)}$	Input capacitance (other pins)	-	-	6	pF
$Z_L$	Input impedance (E2, E1, E0, $\overline{WC}$ ) <sup>(2)</sup>	$V_{IN} < 0.3 V_{CC}$	30	-	kΩ
$Z_H$		$V_{IN} > 0.7 V_{CC}$	500	-	kΩ

1. Specified by design – Not tested in production

2. Evaluated by characterization - Not tested in production. E2, E1, E0 input impedance when the memory is selected (after a Start condition).

**Table 12. AC measurement conditions**

Symbol	Parameter	Min.	Max.	Unit
$C_{bus}$	Load capacitance	-	100	pF
-	SCL input rise/fall time, SDA input fall time	-	50	ns
-	Input levels	0.2 $V_{CC}$ to 0.8 $V_{CC}$		V
-	Input and output timing reference levels	0.3 $V_{CC}$ to 0.7 $V_{CC}$		V

**Figure 14. AC measurement I/O waveform**


DT19774V1

**Table 13. Cycling performance**

Symbol	Parameter	Test condition	Max.	Unit
Ncycle	Write cycle endurance <sup>(1)</sup>	$T_A \leq 25\text{ }^\circ\text{C}$ , $V_{CC}(\text{min}) < V_{CC} < V_{CC}(\text{max})$	4,000,000	Write cycle <sup>(2)</sup>
		$T_A = 85\text{ }^\circ\text{C}$ , $V_{CC}(\text{min}) < V_{CC} < V_{CC}(\text{max})$	1,200,000	

1. The write cycle endurance is defined by characterization and qualification. For devices embedding the ECC functionality (see Section 5.1.5), the write cycle endurance is defined for group of four bytes located at addresses  $[4*N, 4*N+1, 4*N+2, 4*N+3]$  where  $N$  is an integer.
2. A write cycle is executed when either a page write, a byte write, a write identification page or a lock identification page instruction is decoded. When using the byte write, the page write or the write identification page, refer also to Section 5.1.5.

**Table 14. Memory cell data retention**

Parameter	Test condition	Min.	Unit
Data retention <sup>(1)</sup>	$T_A = 55\text{ }^\circ\text{C}$	200	Year

1. The data retention behavior is checked in production, while the data retention limit defined in this table is extracted from characterization and qualification results.

**Table 15. DC characteristics (M24C32-W)**

Symbol	Parameter	Test conditions (in addition to those in Table 7)	Min.	Max.	Unit
$I_{LI}$	Input leakage current (SCL, SDA, $E_i$ )	$V_{IN} = V_{SS}$ or $V_{CC}$ device in standby mode	-	$\pm 2$	$\mu\text{A}$
$I_{LO}$	Output leakage current	SDA in high-Z, external voltage applied on SDA: $V_{SS}$ or $V_{CC}$	-	$\pm 2$	$\mu\text{A}$
$I_{CC}$	Supply current (Read)	$2.5\text{ V} < V_{CC} < 5.5\text{ V}$ , $f_C = 400\text{ kHz}$	-	2	mA
		$2.5\text{ V} < V_{CC} < 5.5\text{ V}$ , $f_C = 1\text{ MHz}$	-	2.5	mA
$I_{CC0}$	Supply current (Write)	During $t_W$ , $2.5\text{ V} \leq V_{CC} \leq 5.5\text{ V}$	-	5 <sup>(1)</sup>	mA
$I_{CC1}$	Standby supply current	Device not selected <sup>(2)</sup> $V_{IN} = V_{SS}$ or $V_{CC}$ , $V_{CC} = 2.5\text{ V}$	-	2	$\mu\text{A}$
		Device not selected <sup>(2)</sup> , $V_{IN} = V_{SS}$ or $V_{CC}$ , $V_{CC} = 5.5\text{ V}$	-	3	$\mu\text{A}$
$V_{IL}$	Input low voltage (SCL, SDA, $\overline{WC}$ , $E_i$ ) <sup>(3)</sup>	-	-0.45	$0.3 V_{CC}$	V
$V_{IH}$	Input high voltage (SCL, SDA)	-	$0.7 V_{CC}$	6.5	V
	Input high voltage ( $\overline{WC}$ , $E_i$ ) <sup>(4)</sup>	-	$0.7 V_{CC}$	$V_{CC}+1$	V
$V_{OL}$	Output low voltage	$I_{OL} = 2.1\text{ mA}$ , $V_{CC} = 2.5\text{ V}$ or $I_{OL} = 3\text{ mA}$ , $V_{CC} = 5.5\text{ V}$	-	0.4	V

1. Evaluated by characterization – not tested in production.
2. The device is not selected after power-up, after a read instruction (after the stop condition), or after the completion of the internal write cycle  $t_W$  ( $t_W$  is triggered by the correct decoding of a write instruction).
3.  $E_i$  inputs should be tied to  $V_{SS}$  (see Section 2.3).
4.  $E_i$  inputs should be tied to  $V_{CC}$  (see Section 2.3).

**Table 16. DC characteristics (M24C32-R)**

Symbol	Parameter	Test conditions <sup>(1)</sup> (in addition to those in Table 8)	Min.	Max.	Unit
$I_{LI}$	Input leakage current (SCL, SDA, $E_i$ )	$V_{IN} = V_{SS}$ or $V_{CC}$ device in standby mode	-	$\pm 2$	$\mu A$
$I_{LO}$	Output leakage current	SDA in high-Z, external voltage applied on SDA: $V_{SS}$ or $V_{CC}$	-	$\pm 2$	$\mu A$
$I_{CC}$	Supply current (Read)	$V_{CC} = 1.8 V$ , $f_C = 400 kHz$	-	0.8	mA
		$f_C = 1 MHz$	-	2.5	mA
$I_{CC0}$	Supply current (write)	During $t_W$ , $1.8 V \leq V_{CC} \leq 2.5 V$	-	3 <sup>(2)</sup>	mA
$I_{CC1}$	Standby supply current	Device not selected <sup>(3)</sup> $V_{IN} = V_{SS}$ or $V_{CC}$ , $V_{CC} = 1.8 V$	-	1	$\mu A$
$V_{IL}$	Input low voltage (SCL, SDA, $\overline{WC}$ , $E_i$ ) <sup>(4)</sup>	$1.8 V \leq V_{CC} < 2.5 V$	-0.45	$0.25 V_{CC}$	V
$V_{IH}$	Input high voltage (SCL, SDA)	$1.8 V \leq V_{CC} < 2.5 V$	$0.75 V_{CC}$	6.5	V
	Input high voltage ( $\overline{WC}$ , $E_i$ ) <sup>(5)</sup>	$1.8 V \leq V_{CC} < 2.5 V$	$0.75 V_{CC}$	$V_{CC}+1$	V
$V_{OL}$	Output low voltage	$I_{OL} = 1 mA$ , $V_{CC} = 1.8 V$	-	0.2	V

1. If the application uses the voltage range R device with  $2.5 V < V_{CC} < 5.5 V$  and  $-40 ^\circ C < T_A < +85 ^\circ C$ , please refer to Table 15 instead of this table.
2. Evaluated by characterization – not tested in production.
3. The device is not selected after power-up, after a read instruction (after the stop condition), or after the completion of the internal write cycle  $t_W$  ( $t_W$  is triggered by the correct decoding of a write instruction).
4.  $E_i$  inputs should be tied to  $V_{SS}$  (see Section 2.3).
5.  $E_i$  inputs should be tied to  $V_{CC}$  (see Section 2.3).

**Table 17. DC characteristics (M24C32-F)**

Symbol	Parameter	Test conditions <sup>(1)</sup> (in addition to those in Table 9)	Min.	Max.	Unit
$I_{LI}$	Input leakage current (SCL, SDA, $E_i$ )	$V_{IN} = V_{SS}$ or $V_{CC}$ device in standby mode	-	$\pm 2$	$\mu A$
$I_{LO}$	Output leakage current	SDA in high-Z, external voltage applied on SDA: $V_{SS}$ or $V_{CC}$	-	$\pm 2$	$\mu A$
$I_{CC}$	Supply current (Read)	$V_{CC} = 1.6 V$ or $1.7 V$ , $f_C = 400 kHz$	-	0.8	mA
		$f_C = 1 MHz$	-	2.5	mA
$I_{CC0}$	Supply current (write)	During $t_W$ , $V_{CC} < 2.5 V$	-	3 <sup>(2)</sup>	mA
$I_{CC1}$	Standby supply current	Device not selected <sup>(3)</sup> $V_{IN} = V_{SS}$ or $V_{CC}$ , $V_{CC} = 1.6 V$ or $1.7 V$	-	1	$\mu A$
$V_{IL}$	Input low voltage (SCL, SDA, $\overline{WC}$ , $E_i$ ) <sup>(4)</sup>	$V_{CC} < 2.5 V$	-0.45	$0.25 V_{CC}$	V
$V_{IH}$	Input high voltage (SCL, SDA)	$V_{CC} < 2.5 V$	$0.75 V_{CC}$	6.5	V
	Input high voltage ( $\overline{WC}$ , $E_i$ ) <sup>(5)</sup>	$V_{CC} < 2.5 V$	$0.75 V_{CC}$	$V_{CC}+1$	V
$V_{OL}$	Output low voltage	$I_{OL} = 1 mA$ , $V_{CC} = 1.6 V$ or $1.7 V$	-	0.2	V

1. If the application uses the voltage range F device with  $2.5 V < V_{CC} < 5.5 V$  and  $-40^\circ C < T_A < +85^\circ C$ , please refer to Table 15 instead of this table.
2. Evaluated by characterization – not tested in production.
3. The device is not selected after power-up, after a read instruction (after the stop condition), or after the completion of the internal write cycle  $t_W$  ( $t_W$  is triggered by the correct decoding of a write instruction).
4.  $E_i$  inputs should be tied to  $V_{SS}$  (see Section 2.3).
5.  $E_i$  inputs should be tied to  $V_{CC}$  (see Section 2.3).

**Table 18. DC characteristics (M24C32-X)**

Symbol	Parameter	Test conditions <sup>(1)</sup> (in addition to those in Table 10)	Min.	Max.	Unit
$I_{LI}$	Input leakage current (SCL, SDA, $E_i$ )	$V_{IN} = V_{SS}$ or $V_{CC}$ device in standby mode	-	$\pm 2$	$\mu A$
$I_{LO}$	Output leakage current	SDA in high-Z, external voltage applied on SDA: $V_{SS}$ or $V_{CC}$	-	$\pm 2$	$\mu A$
$I_{CC}$	Supply current (Read)	$V_{CC} = 1.6 V$ , $f_C = 400 kHz$	-	0.8	mA
		$f_C = 1 MHz$	-	2.5	mA
$I_{CC0}$	Supply current (write)	During $t_W$ , $1.6 V \leq V_{CC} < 2.5 V$	-	3 <sup>(2)</sup>	mA
$I_{CC1}$	Standby supply current	Device not selected <sup>(3)</sup> $V_{IN} = V_{SS}$ or $V_{CC}$ , $V_{CC} = 1.6 V$	-	1	$\mu A$
$V_{IL}$	Input low voltage (SCL, SDA, $\overline{WC}$ , $E_i$ ) <sup>(4)</sup>	$1.6 V \leq V_{CC} < 2.5 V$	-0.45	$0.25 V_{CC}$	V
$V_{IH}$	Input high voltage (SCL, SDA)	$1.6 V \leq V_{CC} < 2.5 V$	$0.75 V_{CC}$	6.5	V
	Input high voltage ( $\overline{WC}$ , $E_i$ ) <sup>(5)</sup>	$1.6 V \leq V_{CC} < 2.5 V$	$0.75 V_{CC}$	$V_{CC}+0.6$	V
$V_{OL}$	Output low voltage	$I_{OL} = 1 mA$ , $V_{CC} = 1.6 V$	-	0.2	V

1. If the application uses the device with  $2.5 V < V_{CC} < 5.5 V$  and  $-20\text{ }^\circ C < T_A < +85\text{ }^\circ C$ , please refer to Table 15 instead of this table.
2. Evaluated by characterization – not tested in production.
3. The device is not selected after power-up, after a read instruction (after the stop condition), or after the completion of the internal write cycle  $t_W$  ( $t_W$  is triggered by the correct decoding of a write instruction).
4.  $E_i$  inputs should be tied to  $V_{SS}$  (see Section 2.3).
5.  $E_i$  inputs should be tied to  $V_{CC}$  (see Section 2.3).



**Table 19. AC characteristics (Fast mode)**

Symbol	Alt.	Parameter	Min.	Max.	Unit
$f_C$	$f_{SCL}$	Clock frequency	-	400	kHz
$t_{CHCL}$	$t_{HIGH}$	Clock pulse width high	600	-	ns
$t_{CLCH}$	$t_{LOW}$	Clock pulse width low	1300	-	ns
$t_{QL1QL2}^{(1)}$	$t_F$	SDA (out) fall time	20 <sup>(2)</sup>	300	ns
$t_{XH1XH2}$	$t_R$	Input signal rise time	(3)	(3)	ns
$t_{XL1XL2}$	$t_F$	Input signal fall time	(3)	(3)	ns
$t_{DXCH}$	$t_{SU:DAT}$	Data in setup time	100	-	ns
$t_{CLDX}$	$t_{HD:DAT}$	Data in hold time	0	-	ns
$t_{CLQX}^{(4)}$	$t_{DH}$	Data out hold time	100	-	ns
$t_{CLQV}^{(5)}$	$t_{AA}$	Clock low to next data valid (access time)	-	900	ns
$t_{CHDL}$	$t_{SU:STA}$	Start condition setup time	600	-	ns
$t_{DLCL}$	$t_{HD:STA}$	Start condition hold time	600	-	ns
$t_{CHDH}$	$t_{SU:STO}$	Stop condition set up time	600	-	ns
$t_{DHDL}$	$t_{BUF}$	Time between Stop condition and next Start condition	1300	-	ns
$t_{WLDL}^{(1)(6)}$	$t_{SU:WC}$	$\overline{WC}$ set up time (before the start condition)	0	-	$\mu$ s
$t_{DHWL}^{(1)(7)}$	$t_{HD:WC}$	$\overline{WC}$ hold time (after the stop condition)	1	-	$\mu$ s
$t_W$	$t_{WR}$	Internal Write cycle duration	-	5 <sup>(8)</sup>	ms
$t_{NS}^{(1)}$	-	Pulse width ignored (input filter on SCL and SDA) - single glitch	-	80	ns

1. Evaluated by characterization - Not tested in production.

2. With  $C_L = 10$  pF.

3. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the I<sup>2</sup>C specification that the input signal rise and fall times be more than 20 ns and less than 300 ns when  $f_C < 400$  kHz.

4. To avoid spurious start and stop conditions, a minimum delay is placed between  $SCL=1$  and the falling or rising edge of SDA.

5.  $t_{CLQV}$  is the time (from the falling edge of SCL) required by the SDA bus line to reach either  $0.3V_{CC}$  or  $0.7V_{CC}$ , assuming that the  $R_{bus} \times C_{bus}$  time constant is within the values specified in Figure 15

6.  $\overline{WC} = 0$  setup time condition to enable the execution of a write command.

7.  $\overline{WC} = 0$  hold time condition to enable the execution of a write command.

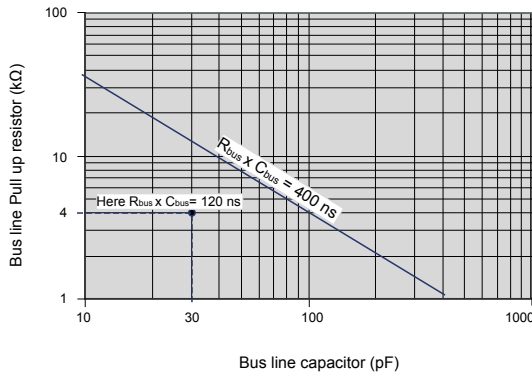
8. 10 ms for the M24C32-X.

**Table 20. AC characteristics (Fast mode Plus)**

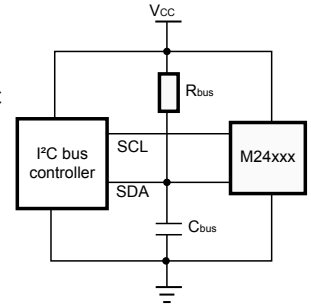
Symbol	Alt.	Parameter	Min.	Max.	Unit
$f_C$	$f_{SCL}$	Clock frequency	-	1	MHz
$t_{CHCL}$	$t_{HIGH}$	Clock pulse width high	260	-	ns
$t_{CLCH}$	$t_{LOW}$	Clock pulse width low	500	-	ns
$t_{XH1XH2}$	$t_R$	Input signal rise time	(1)	(1)	ns
$t_{XL1XL2}$	$t_F$	Input signal fall time	(1)	(1)	ns
$t_{QL1QL2}^{(2)}$	$t_F$	SDA (out) fall time	20	120	ns
$t_{DXCH}$	$t_{SU:DAT}$	Data in setup time	50	-	ns
$t_{CLDX}$	$t_{HD:DAT}$	Data in hold time	0	-	ns
$t_{CLQX}^{(4)}$	$t_{DH}$	Data out hold time	100	-	ns
$t_{CLQV}^{(5)}$	$t_{AA}$	Clock low to next data valid (access time)	-	450	ns
$t_{CHDL}$	$t_{SU:STA}$	Start condition setup time	250	-	ns
$t_{DLCL}$	$t_{HD:STA}$	Start condition hold time	250	-	ns
$t_{CHDH}$	$t_{SU:STO}$	Stop condition setup time	250	-	ns
$t_{DHDL}$	$t_{BUF}$	Time between Stop condition and next Start condition	500	-	ns
$t_{WLDL}^{(2)(6)}$	$t_{SU:WC}$	$\overline{WC}$ set up time (before the start condition)	0	-	$\mu$ s
$t_{DHWL}^{(2)(7)}$	$t_{HD:WC}$	$\overline{WC}$ hold time (after the stop condition)	1	-	$\mu$ s
$t_W$	$t_{WR}$	Write cycle time	-	5 <sup>(8)</sup>	ms
$t_{NS}^{(2)}$	-	Pulse width ignored (input filter on SCL and SDA)	-	80	ns

1. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the I<sup>2</sup>C specification that the input signal rise and fall times be less than 120 ns when  $f_C < 1$  MHz.
2. Evaluated by characterization - Not tested in production.
3. With  $C_L = 10$  pF.
4. To avoid spurious Start and Stop conditions, a minimum delay is placed between  $SCL=1$  and the falling or rising edge of SDA.
5.  $t_{CLQV}$  is the time (from the falling edge of SCL) required by the SDA bus line to reach either  $0.3 V_{CC}$  or  $0.7 V_{CC}$ , assuming that the  $R_{bus} \times C_{bus}$  time constant is within the values specified in Figure 16.
6.  $\overline{WC} = 0$  setup time condition to enable the execution of a write command.
7.  $\overline{WC} = 0$  hold time condition to enable the execution of a write command.
8. 10 ms for the M24C32-X..

**Figure 15. Maximum  $R_{bus}$  value versus bus parasitic capacitance ( $C_{bus}$ ) for an I<sup>2</sup>C<sub>bus</sub> at maximum frequency  $f_c = 400$  kHz**

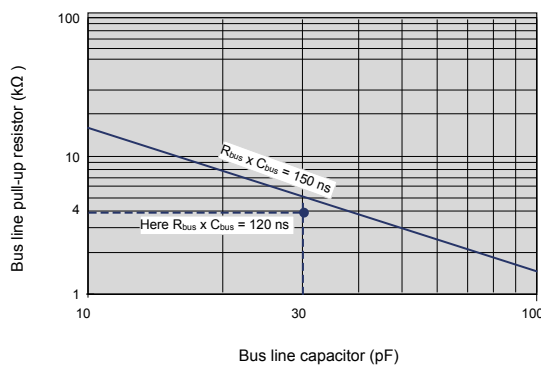


The  $R_{bus} \times C_{bus}$  time constant must be below the 400 ns time constant line represented on the left

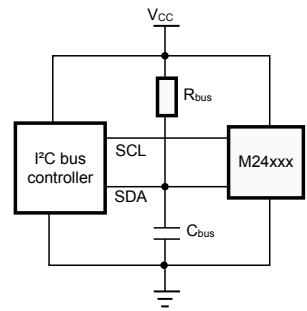


DT137916V4

**Figure 16. Maximum  $R_{bus}$  value versus bus parasitic capacitance ( $C_{bus}$ ) for an I<sup>2</sup>C bus at maximum frequency  $f_c = 1$  MHz**

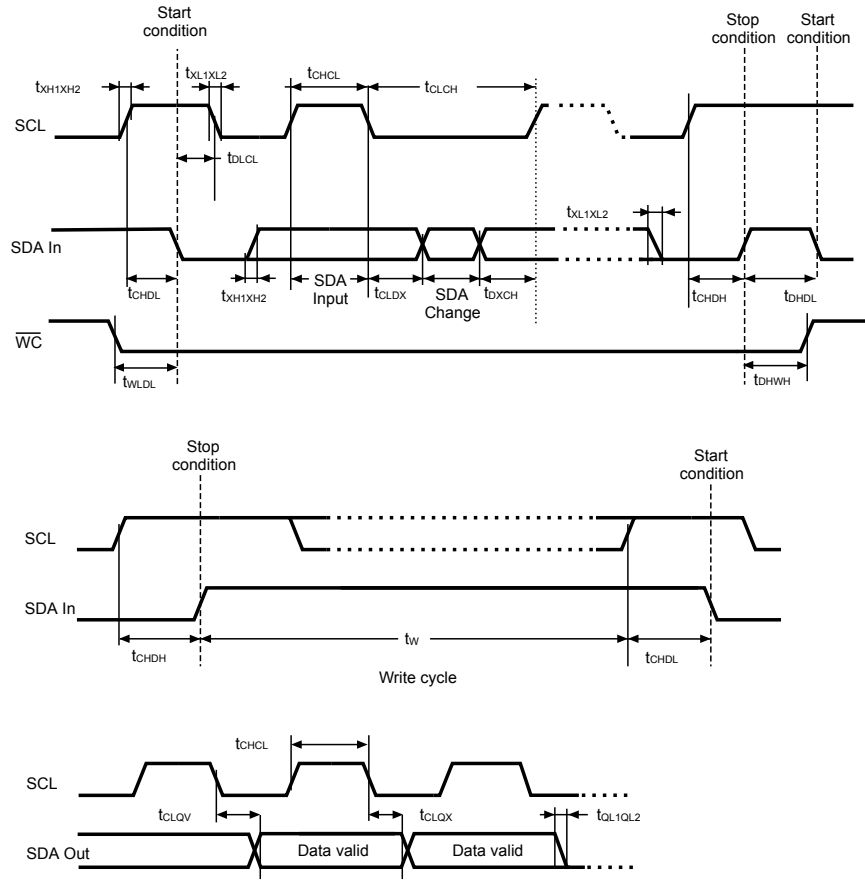


The  $R_{bus} \times C_{bus}$  time constant must be below the 150 ns time constant line represented on the left



DT19745V7

Figure 17. AC waveforms



DT007951V1



## 9 Package information

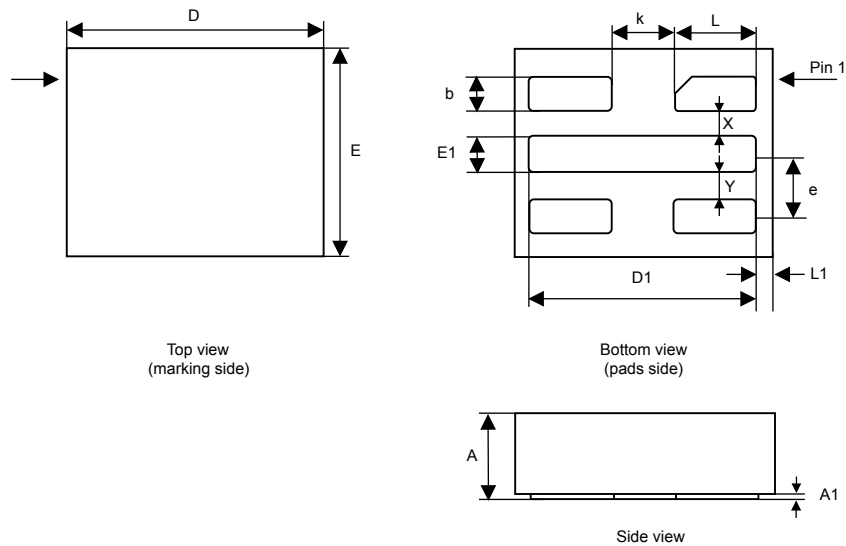
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In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

## 9.1 UFDFPN5 (DFN5) package information

UFDFPN5 is a 5-lead, 1.7 × 1.4 mm, 0.55 mm thickness, ultra thin fine pitch dual flat package.

Figure 18. UFDFPN5 - Outline



A0UK\_UFDFPN5\_ME\_V3

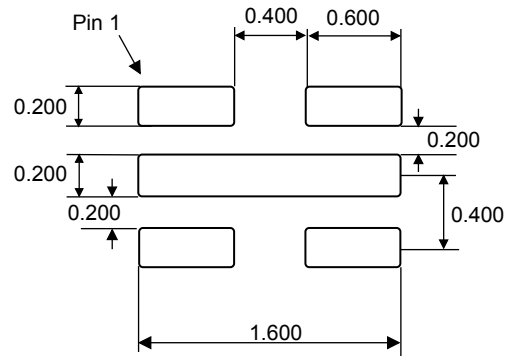
1. Maximum package warpage is 0.05 mm.
2. Exposed copper is not systematic and can appear partially or totally according to the cross section.
3. Drawing is not to scale.
4. On the bottom side, pin 1 is identified by the specific pad shape and, on the top side, pin 1 is defined from the orientation of the marking. When reading the marking, pin 1 is below the upper left package corner.

Table 21. UFDFPN5 - Mechanical data

Symbol	millimeters			inches		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	-	0.050	0.0000	-	0.0020
b <sup>(1)</sup>	0.175	0.200	0.225	0.0069	0.0079	0.0089
D	1.600	1.700	1.800	0.0630	0.0669	0.0709
D1	1.400	1.500	1.600	0.0551	0.0591	0.0630
E	1.300	1.400	1.500	0.0512	0.0551	0.0591
E1	0.175	0.200	0.225	0.0069	0.0079	0.0089
X	-	0.200	-	-	0.0079	-
Y	-	0.200	-	-	0.0079	-
e	-	0.400	-	-	0.0157	-
L	0.500	0.550	0.600	0.0197	0.0217	0.0236
L1	-	0.100	-	-	0.0039	-
k	-	0.400	-	-	0.0157	-

1. Dimension b applies to plated terminal and is measured between 0.15 and 0.30mm from the terminal tip.

Figure 19. UFDFPN5 - Footprint example



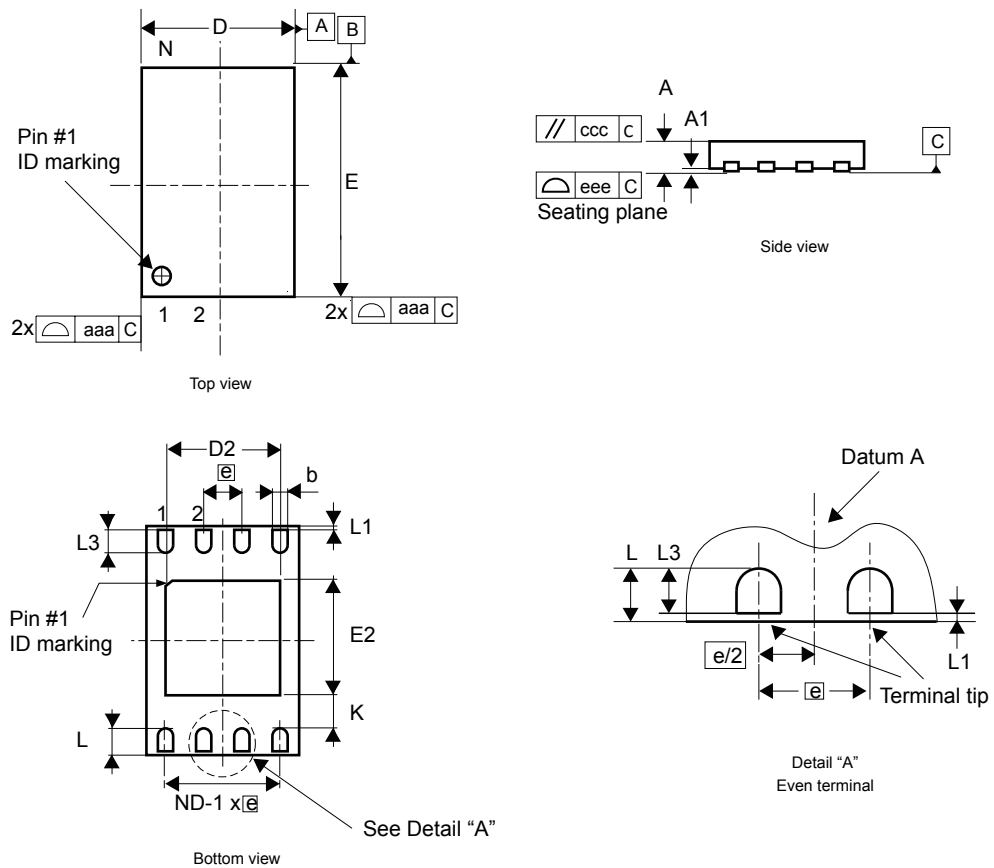
A0UK\_UFDFPN5\_FP\_V1

1. Dimensions are expressed in millimeters.

## 9.2 UFDFPN8 (DFN8) package information

This UFDFPN is a 8-lead, 2 x 3 mm, 0.5 mm pitch ultra thin profile fine pitch dual flat package.

Figure 20. UFDFPN8 - Outline



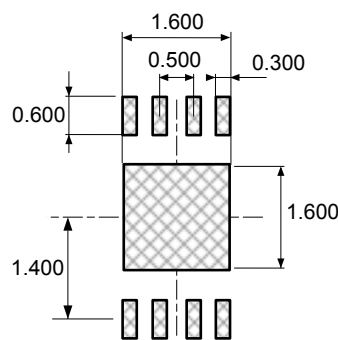
1. Maximum package warpage is 0.05 mm.
2. Exposed copper is not systematic and can appear partially or totally according to the cross section.
3. Drawing is not to scale.
4. The central pad (the area E2 by D2 in the above illustration) must be either connected to  $V_{SS}$  or left floating (not connected) in the end application.



**Table 22. UFDFPN8 - Mechanical data**

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
A	0.450	0.550	0.600	0.0177	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
b <sup>(2)</sup>	0.200	0.250	0.300	0.0079	0.0098	0.0118
D	1.900	2.000	2.100	0.0748	0.0787	0.0827
D2	1.200	-	1.600	0.0472	-	0.0630
E	2.900	3.000	3.100	0.1142	0.1181	0.1220
E2	1.200	-	1.600	0.0472	-	0.0630
e	-	0.500	-	-	0.0197	-
K	0.300	-	-	0.0118	-	-
L	0.300	-	0.500	0.0118	-	0.0197
L1	-	-	0.150	-	-	0.0059
L3	0.300	-	-	0.0118	-	-
aaa	-	-	0.150	-	-	0.0059
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee <sup>(3)</sup>	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to four decimal digits.
2. Dimension *b* applies to plated terminal and is measured between 0.15 and 0.30 mm from the terminal tip.
3. Applied for exposed die paddle and terminals. Exclude embedding part of exposed die paddle from measuring.

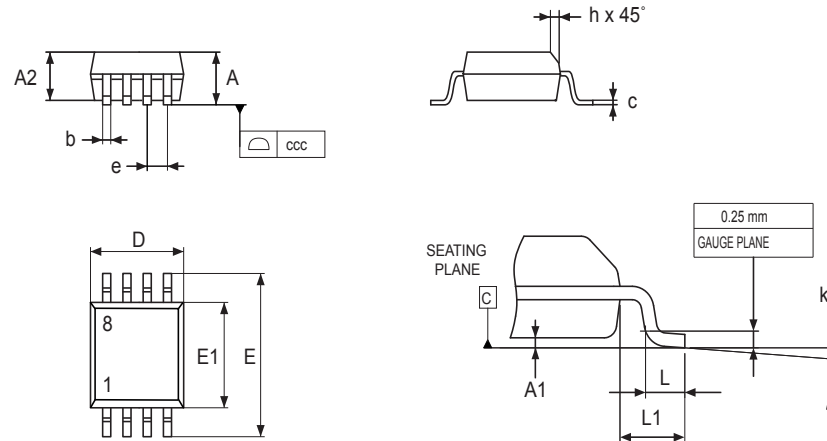
**Figure 21. UFDFPN8 - Footprint example**


1. Dimensions are expressed in millimeters.

### 9.3 SO8N package information

This SO8N is an 8-lead, 4.9 x 6 mm, plastic small outline, 150 mils body width, package.

**Figure 22. SO8N – Outline**



07\_SO8\_ME\_V2

1. Drawing is not to scale.

**Table 23. SO8N – Mechanical data**

Symbol	millimeters			inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.750	-	-	0.0689
A1	0.100	-	0.250	0.0039	-	0.0098
A2	1.250	-	-	0.0492	-	-
b	0.280	-	0.480	0.0110	-	0.0189
c	0.170	-	0.230	0.0067	-	0.0091
D <sup>(2)</sup>	4.800	4.900	5.000	0.1890	0.1929	0.1969
E	5.800	6.000	6.200	0.2283	0.2362	0.2441
E1 <sup>(3)</sup>	3.800	3.900	4.000	0.1496	0.1535	0.1575
e	-	1.270	-	-	0.0500	-
h	0.250	-	0.500	0.0098	-	0.0197
k	0°	-	8°	0°	-	8°
L	0.400	-	1.270	0.0157	-	0.0500
L1	-	1.040	-	-	0.0409	-
ccc	-	-	0.100	-	-	0.0039

1. Values in inches are converted from mm and rounded to four decimal digits.

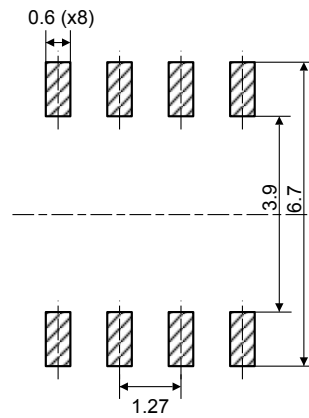
2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per side

3. Dimension "E1" does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25 mm per side.

Note:

The package top may be smaller than the package bottom. Dimensions D and E1 are determined at the outermost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interleads flash, but including any mismatch between the top and bottom of plastic body. Measurement side for mold flash, protrusions or gate burrs is bottom side.

Figure 23. SO8N - Footprint example



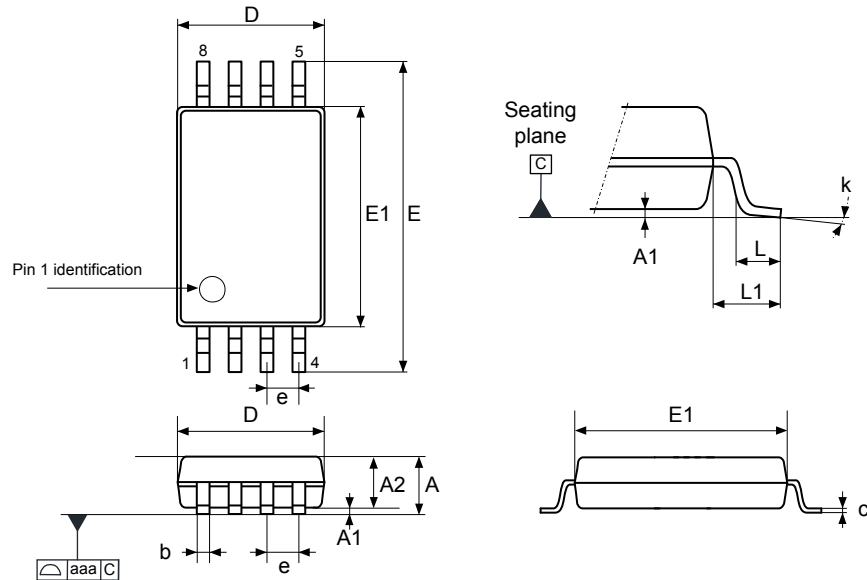
07\_SO8N\_FP\_V2

1. Dimensions are expressed in millimeters.

## 9.4 TSSOP8 package information

This TSSOP is an 8-lead, 3 x 6.4 mm, 0.65 mm pitch, thin shrink small outline package.

**Figure 24. TSSOP8 – Outline**



DT\_6P\_A\_TSSOP8\_ME\_V4

1. Drawing is not to scale.

**Table 24. TSSOP8 – Mechanical data**

Symbol	millimeters			inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
c	0.090	-	0.200	0.0035	-	0.0079
D <sup>(2)</sup>	2.900	3.000	3.100	0.1142	0.1181	0.1220
e	-	0.650	-	-	0.0256	-
E	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1 <sup>(3)</sup>	4.300	4.400	4.500	0.1693	0.1732	0.1772
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	-	8°	0°	-	8°
aaa	-	-	0.100	-	-	0.0039

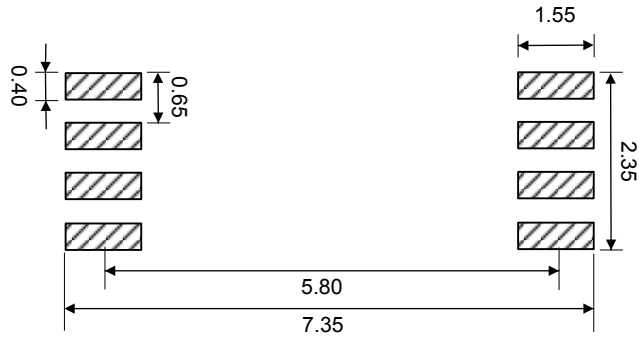
1. Values in inches are converted from mm and rounded to four decimal digits.

2. Dimension "D" does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

3. Dimension "E1" does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25 mm per side.

Note: The package top may be smaller than the package bottom. Dimensions D and E1 are determined at the outermost extremes of the plastic body exclusive of the mold flash, tie bar burrs, gate burrs, and interleads flash, but including any mismatch between the top and bottom of the plastic body. The measurement side for the mold flash, protrusions, or gate burrs is the bottom side.

Figure 25. TSSOP8 – Footprint example



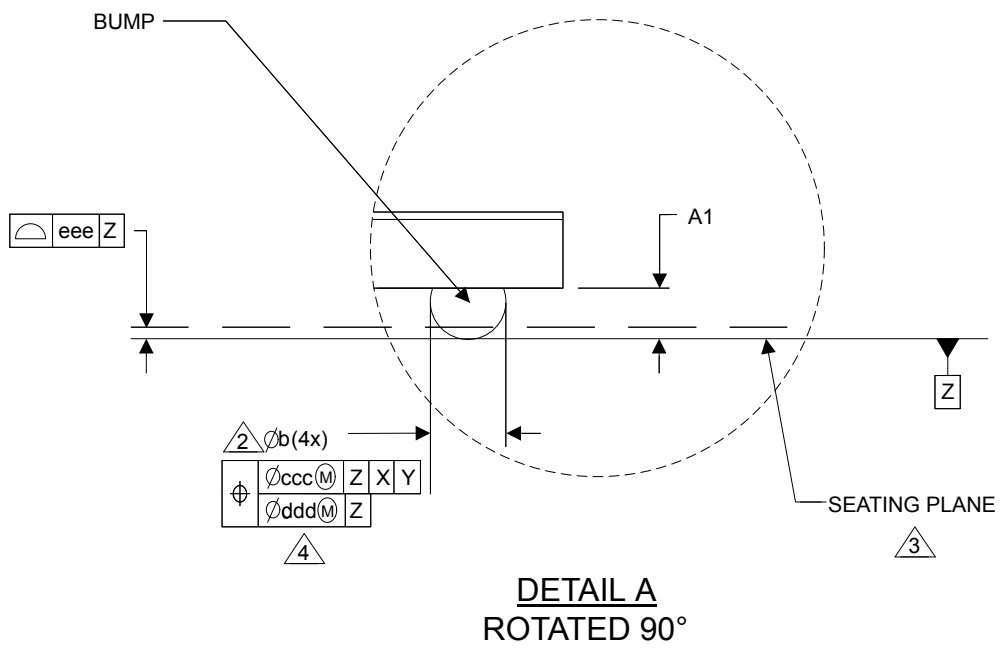
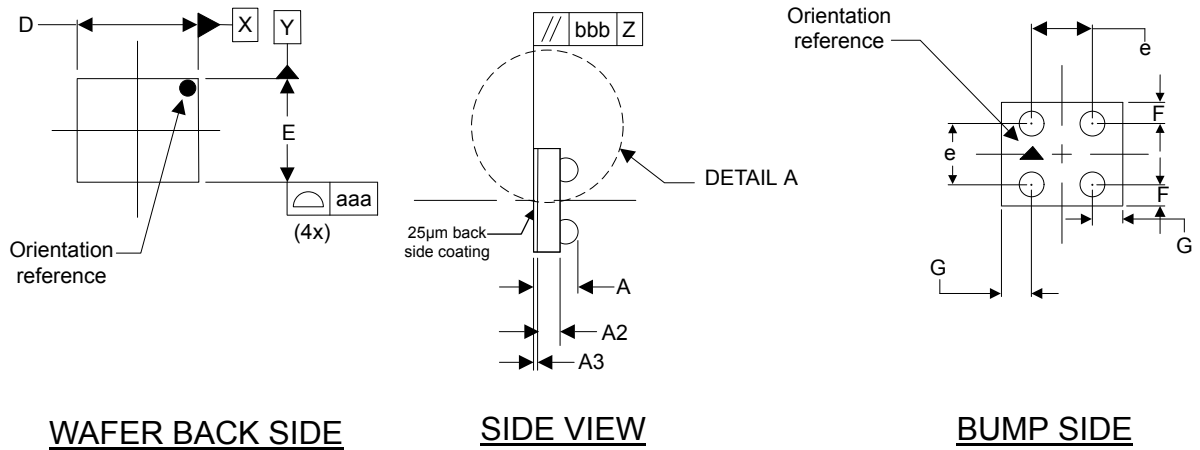
DI\_6P\_TSSOP8\_FP\_V2

1. Dimensions are expressed in millimeters.

### 9.5 WLCSP4 package information with BSC

This WLCSP is a 4-ball, 0.795 x 0.674 mm, wafer level chip scale package.

Figure 26. WLCSP4 - Outline



1. Drawing is not to scale.
2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.
3. Primary datum Z and seating plane are defined by the spherical crowns of the bump.
4. Bump position designation per JESD 95-1, SPP-010.

PT\_WLCSP4\_F8H\_P4\_withBSC\_ME\_V1

**Table 25. WLCSP4 - Mechanical data**

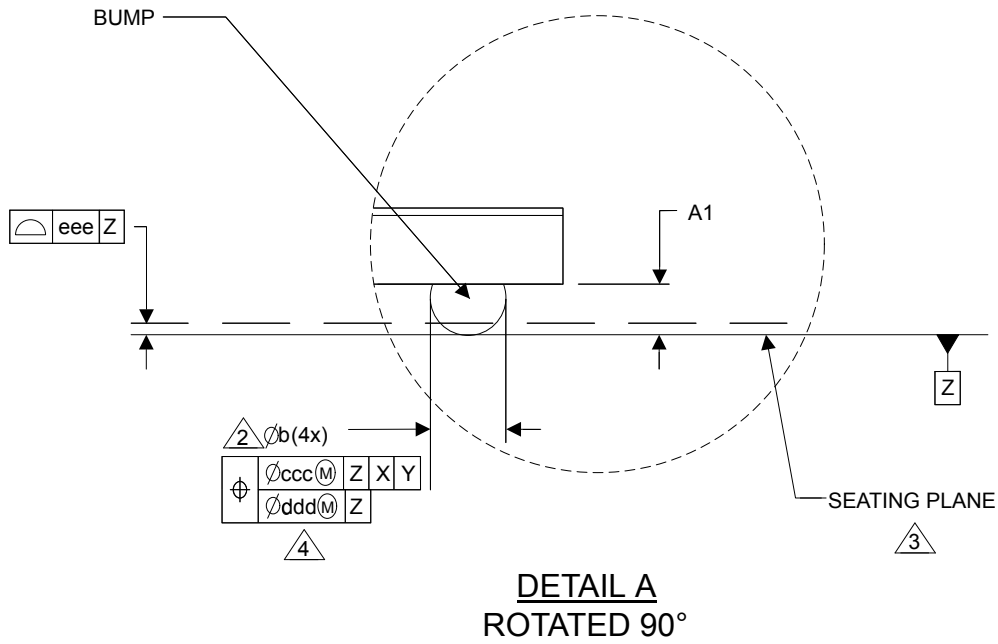
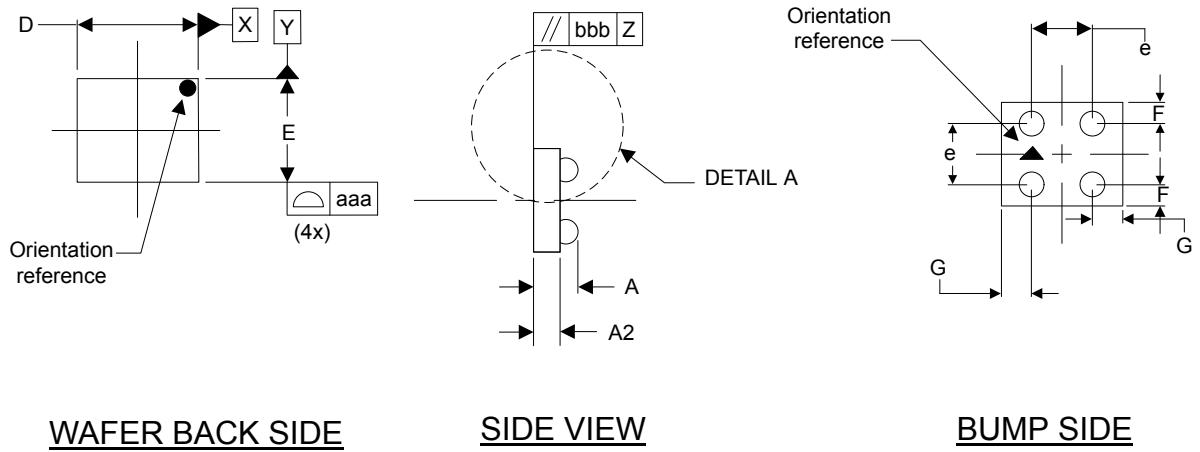
Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
A	0.285	0.315	0.345	0.0102	0.0114	0.0126
A1	-	0.115	-	-	0.0045	-
A2	-	0.175	-	-	0.0069	-
A3	-	0.025 BSC	-	-	0.0010 BSC	-
Øb	-	0.160	-	-	0.0063	-
D	-	0.795	0.815	-	0.0313	0.0321
E	-	0.674	0.694	-	0.0265	0.0273
e	-	0.400	-	-	0.0157	-
F	-	0.137	-	-	0.0054	-
G	-	0.198	-	-	0.0078	-
N <sup>(2)</sup>	4					
aaa	-	0.11	-	-	0.0043	-
bbb	-	0.11	-	-	0.0043	-
ccc	-	0.11	-	-	0.0043	-
ddd	-	0.06	-	-	0.0024	-
eee	-	0.06	-	-	0.0024	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. N is the total number of terminals.

### 9.6 WLCSP4 package information without BSC

This WLCSP is a 4-ball, 0.795 x 0.674 mm, wafer level chip scale package.

Figure 27. WLCSP4 - Outline



1. Drawing is not to scale.
2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.
3. Primary datum Z and seating plane are defined by the spherical crowns of the bump.
4. Bump position designation per JESD 95-1, SPP-010.

PT\_WLCSP4\_F8H\_P4\_withoutBSC\_ME\_V1



**Table 26. WLCSP4 - Mechanical data**

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
A	0.260	0.290	0.320	0.0102	0.0114	0.0126
A1	-	0.115	-	-	0.0045	-
A2	-	0.175	-	-	0.0069	-
Øb	-	0.160	-	-	0.0063	-
D	-	0.795	0.815	-	0.0313	0.0321
E	-	0.674	0.694	-	0.0265	0.0273
e	-	0.400	-	-	0.0157	-
F	-	0.137	-	-	0.0054	-
G	-	0.198	-	-	0.0078	-
N <sup>(2)</sup>	4					
aaa	-	0.11	-	-	0.0043	-
bbb	-	0.11	-	-	0.0043	-
ccc	-	0.11	-	-	0.0043	-
ddd	-	0.06	-	-	0.0024	-
eee	-	0.06	-	-	0.0024	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.

2. N is the total number of terminals.

## 10 Ordering information

**Table 27. Ordering information scheme**

Example:	M24	C32	- D	W	MC	6	T	P	/T	F
<b>Device type</b>										
M24 = I <sup>2</sup> C serial access EEPROM										
<b>Device function</b>										
C32 = 32 Kbit (4096 x 8 bit)										
<b>Device family</b>										
Blank = Without identification page										
D = With identification page										
<b>Operating voltage</b>										
W = V <sub>CC</sub> = 2.5 V to 5.5 V										
R = V <sub>CC</sub> = 1.8 V to 5.5 V										
F = V <sub>CC</sub> = 1.7 V to 5.5 V										
X = V <sub>CC</sub> = 1.6 V to 5.5 V										
<b>Package <sup>(1)</sup></b>										
MN = SO8 (150 mil width)										
DW = TSSOP8 (169 mil width)										
MC = UDFPN8 (DFN8)										
MH = UDFPN5 (DFN5)										
CU = Ultra-thin 4 bump WLCSP										
<b>Device grade</b>										
6 = Industrial: device tested with standard test flow over -40 to 85 °C										
5 = Consumer: device tested with standard test flow over -20 to 85 °C										
<b>Option</b>										
T = Tape and reel packing										
blank = tube packing										
<b>Plating technology</b>										
P or G = ECOPACK2®										
<b>Process <sup>(2)(3)</sup></b>										
/K or /T= Manufacturing technology code										
<b>Option</b>										
Blank = No back side coating										
F = Back side coating										

1. ECOPACK2 (RoHS compliant and free of brominated, chlorinated and antimony oxide flame retardants).
2. These process letters appear on the device package (marking) and on the shipment box. Please contact your nearest ST Sales Office for further information.
3. Part numbering for WLCSP

**Note:** For a list of available options (memory, package, and so on) or for further information on any aspect of this device, contact your nearest ST sales office.

**Note:** Parts marked as "ES" or "E" are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

**Table 28. Ordering information scheme (unsawn wafer)**

Example:	M24	C32 -	F	T	W	20	I	/90
<b>Device type</b>	<div style="border: 1px solid black; padding: 5px;"> <p>M24 = I<sup>2</sup>C serial access EEPROM</p> <p>C32 = 32 Kbit (4096 x 8 bit)</p> <p>F = V<sub>CC</sub> = 1.7 V to 5.5 V</p> <p>T = F8H</p> <p>W = wafer (bare die)</p> <p>20 = Non-backlapped wafer</p> <p>I = Inkless test</p> <p>90 = -40°C to 85°C</p> </div>							
<b>Device function</b>								
<b>Operating voltage</b>								
<b>Process</b>								
<b>Delivery form</b>								
<b>Wafer thickness</b>								
<b>Wafer testing</b>								
<b>Device grade</b>								

*Note:* For all information concerning the M24C32 delivered in unsawn wafer, please contact your nearest ST Sales Office.

### Engineering samples

Parts marked as ES or E are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences deriving from such use. In no event, will ST be liable for the customer using of these engineering samples in production. ST's quality department must be contacted prior to any decision to use these engineering samples to run qualification activity.

## Revision history

**Table 29. Document revision history**

Date	Version	Changes
18-Mar-2011	18	<p>Added:</p> <ul style="list-style-type: none"> <li>M24C32-DF and all information concerning the Identification page: sections 4.9, 4.10, 4.17, 4.18</li> <li>ECC section 4.11</li> <li>AC table with clock frequency of 1 MHz (Table 18)</li> <li>Table 4: Device select code</li> </ul> <p>Updated:</p> <ul style="list-style-type: none"> <li>Section 1: Description</li> <li>Section 4.5: Memory addressing</li> <li>Section 4.18: Read the lock status (M24C32-D)</li> <li>Table 6: Absolute maximum ratings</li> <li>AC/DC tables 13, 17 with values specific to the device identified with process letter K</li> </ul> <p>Deleted:</p> <ul style="list-style-type: none"> <li>Table 2: Device select code</li> <li>Table 23: Available M24C32 products (package, voltage range, temperature grade)</li> </ul>
14-Sep-2011	19	<p>Updated:</p> <ul style="list-style-type: none"> <li>Figure 4: I2C Fast mode (<math>f_C = 400</math> kHz): maximum Rbus value versus bus parasitic capacitance (Cbus)</li> <li>Figure 5: I2C Fast mode Plus (<math>f_C = 1</math> MHz): maximum Rbus value versus bus parasitic capacitance (Cbus)</li> </ul> <p>Added <math>t_{WLDL}</math> and <math>t_{DHWL}</math> in:</p> <ul style="list-style-type: none"> <li>Table 17: 400 kHz AC characteristics</li> <li>Table 18: 1 MHz AC characteristics</li> <li>Figure 13: AC waveforms</li> </ul> <p>Minor text changes.</p>
21-May-2012	20	<p>Datasheet split into:</p> <ul style="list-style-type: none"> <li>M24C32-DF, M24C32-W, M24C32-R, M24C32-F (this datasheet) for standard products (range 6),</li> <li>M24C32-125 datasheet for automotive products (range 3).</li> </ul>
25-Jul-2012	21	<p>Added reference M24C32-X.</p> <p>Updated:</p> <ul style="list-style-type: none"> <li>AC and DC tables in Section 8: DC and AC parameters.</li> <li>Figure 56.: M24C16-FCS5TP/S WLCSP 5 bumps package outline.</li> </ul>
19-May-2014	22	<p>Add new package UFDFPN5, description on Figure 51 and Table 20.</p> <p>Updated:</p> <ul style="list-style-type: none"> <li>Figure 30: Block diagram</li> <li>VESD value on Table 14</li> <li>Icc1 values on Table 32</li> <li>Icc and Icc0 test conditions on Table 40</li> <li>VIH(max) values on Table 32, Table 33</li> <li>Icc, Icc0, Icc1, VIL, VOL and VIH test conditions on Table 40</li> <li>Note on Table 29, Table 31, Table 32, Table 40, Table 41 and Table 48</li> <li>Table 76</li> <li>Section numbering for Section 5.2.5 and Section 5.2.6.</li> </ul>
28-Jul-2014	23	Updated Table 21.
02-Sept-2014	24	<p>Updated</p> <ul style="list-style-type: none"> <li>Section 5.1.6.</li> <li>Note 1 on Table 29</li> </ul>

Date	Version	Changes
		<ul style="list-style-type: none"> <li>• Section 9, added reference to unsawn wafer availability.</li> <li>• note 3 on Table 76.</li> </ul> <p>Added:</p> <ul style="list-style-type: none"> <li>• Note 1 on Table 21</li> <li>• Note 2 on Table 31</li> <li>• Note 2 on Figure 58</li> <li>• Table 90.</li> </ul> <p>Removed notes 1 and 2 on Section 5.1.6</p>
23-Jul-2015	25	<p>Updated:</p> <ul style="list-style-type: none"> <li>• Section 2.4</li> <li>• Section 6</li> <li>• Table 76</li> <li>• note 2 on Table 76</li> </ul> <p>Added:</p> <ul style="list-style-type: none"> <li>• WLCSP package in cover page.</li> <li>• Section 9.7: Ultra Thin WLCSP package information</li> </ul>
27-Aug-2015	26	<p>Updated:</p> <ul style="list-style-type: none"> <li>• Table 14</li> </ul> <p>Added:</p> <ul style="list-style-type: none"> <li>• Note 3 in Figure 59.</li> <li>• Note 1 in Table 60.</li> <li>• Note 2 Table 76</li> </ul>
12-Feb-2016	27	Updated Figure 17, Figure 51. Added Table 2.
05-May-2016	28	Updated Table 14: Absolute maximum ratings.
10-Jul-2017	29	Updated Section 9.6: Ultra Thin WLCSP package information.
11-Sep-2017	30	Added reference to DFN8 and DFN5 in: cover page figure, Figure 3: UFDFPN5 (DFN5) package connections, Section 9.1: UFDFPN5 (DFN5) package information, Section 9.2: UFDFPN8 (DFN8) package information and Table 28: Ordering information scheme
01-Dec-2023	31	<p>Updated:</p> <ul style="list-style-type: none"> <li>• <a href="#">Section Cover images.</a></li> <li>• <a href="#">Section Features.</a></li> <li>• <a href="#">Figure 1.</a></li> <li>• <a href="#">Section 3 Memory organization.</a></li> <li>• <a href="#">Section 4.5 Device addressing.</a></li> </ul> <p>Minor text changes.</p> <p>New stylesheet.</p>

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